

## HALF-BRIDGE DRIVER

#### **Features**

- Floating channel designed for bootstrap operation
- Fully operational to +600V
- Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 5V to 20V
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- High side output in phase with input
- Internal 450ns dead-time
- Lower di/dt gate driver for better noise immunity
- Shut down input turns off both channels
- · Leadfree, RoHS compliant

#### **Typical Applications**

- Appliance motor drives
- Servo drives
- Micro inverter drives
- General purpose three phase inverters

#### **Product Summary**

V <sub>OFFSET</sub>	600V Max
V <sub>OUT</sub>	5V – 20V
I <sub>o+</sub> & I <sub>o-</sub> (typical)	200mA / 350mA
t <sub>ON</sub> & t <sub>OFF</sub> (typical)	650ns / 200ns
Delay Matching	50ns

## **Package Options**



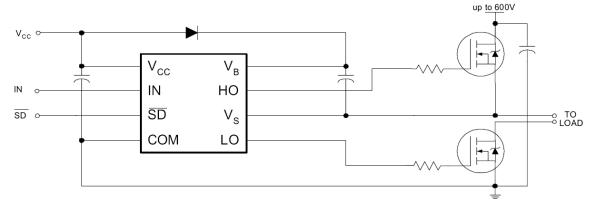
**Ordering Information** 

Base Part Number	Pookogo Typo	Standard I	Pack	Complete Part Number
base Part Number	Package Type	Form Quantity		Complete Part Number
IRS2302S	SOIC8N	Tube/Bulk	95	IRS2302SPBF
11/323023	SOICON	Tape and Reel	2500	IRS2302STRPBF



## **Typical Connection Diagram**

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(Refer to Lead Assignments for correct pin configuration). This diagram shows electrical connections only. Please refer to our Application Notes and Design Tips for proper circuit board layout.



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### **Description**

The IRS2302S is a high voltage, high speed power MOSFET and IGBT driver with independent high- and low-side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high-side configuration which operates up to 600V.



### **Absolute Maximum Ratings**

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
V <sub>B</sub>	High-side floating absolute voltage	-0.3	625	
Vs	High-side floating supply offset voltage	V <sub>B</sub> - 25	V <sub>B</sub> + 0.3	
$V_{HO}$	High-side floating output voltage	V <sub>S</sub> - 0.3	$V_B + 0.3$	V
V <sub>CC</sub>	Low-side and logic fixed supply voltage	-0.3	25	V
$V_{LO}$	Low-side output voltage	-0.3	V <sub>CC</sub> + 0.3	
V <sub>IN</sub>	Logic input voltage (IN & SD)	COM -0.3	V <sub>CC</sub> + 0.3	
dV <sub>S</sub> /dt	Allowable offset supply voltage transient	_	50	V/ns
$P_D$	Package power dissipation @ TA ≤ 25°C	_	0.625	W
Rth <sub>JA</sub>	Thermal resistance, junction to ambient	_	200	°C/W
TJ	Junction temperature	_	150	
Ts	Storage temperature	-50	150	°C
T <sub>L</sub>	Lead temperature (soldering, 10 seconds)	_	300	

#### **Recommended Operating Conditions**

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The input/output logic timing diagram is shown in Fig. 1. For proper operation the device should be used within the recommended conditions. The  $V_S$  offset rating is tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
$V_B$	High-side floating supply absolute voltage	V <sub>S</sub> + 5	V <sub>S</sub> + 20	
Vs	High-side floating supply offset voltage	† 1	600	
$V_{HO}$	High-side floating output voltage	Vs	V <sub>B</sub>	V
V <sub>cc</sub>	Low-side and logic fixed supply voltage	5	20	V
V <sub>LO</sub>	Low-side output voltage	0	V <sub>CC</sub>	
V <sub>IN</sub>	Logic input voltage (IN & SD)	СОМ	V <sub>CC</sub>	
T <sub>A</sub>	Ambient temperature	-40	125	°C

<sup>†:</sup> Logic operational for  $V_S$  of -5 V to +600 V. Logic state held for  $V_S$  of -5 V to  $-V_{BS}$ .

(Please refer to the Design Tip DT97 -3 for more details).



#### **Static Electrical Characteristics**

 $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V and  $T_A$  = 25°C unless otherwise specified. The  $V_{IL}$ ,  $V_{IH}$  and  $I_{IN}$  parameters are referenced to COM and are applicable to the respective input leads: IN and SD. The  $V_{O_i}$   $I_{O_i}$  and  $R_{on}$  parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min	Тур	Max	Units	Test conditions
V <sub>IH</sub>	Logic "1" input voltage	2.5	_	_	V	\/ = 40\/ to 20\/
V <sub>IL</sub>	Logic "0" input voltage	_	_	0.8	V	V <sub>CC</sub> = 10V to 20V
$V_{OH}$	High level output voltage, $V_{\text{BIAS}}$ - $V_{\text{O}}$	_	_	0.2	V	I <sub>O</sub> = 2mA
$V_{\text{OL}}$	Low level output voltage, V <sub>O</sub>	_	_	0.1	V	1 <sub>0</sub> – 2111A
$V_{SD, TH+}$	SD input positive going threshold	2.5	_	_	V	Vcc = 10V to 20V
$V_{\text{SD, TH-}}$	SD input negative going threshold	_	_	0.8	V	VCC = 10V to 20V
$I_{LK}$	Offset supply leakage current	_	_	50		V <sub>B</sub> = V <sub>S</sub> = 600V
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> supply current	40	140	240	μA	V <sub>IN</sub> = 0V or 5V
I <sub>QCC</sub>	Quiescent V <sub>CC</sub> supply current	0.4	1.0	1.6	mA	
I <sub>IN+</sub>	Logic "1" input bias current	_	5	20		IN = 5V, SD = 0V
I <sub>IN-</sub>	Logic "0" input bias current	_	_	5	μA	IN = 0V, SD = 5V
$V_{\text{CCUV+}}$ $V_{\text{BSUV+}}$	$V_{\text{CC}}$ and $V_{\text{BS}}$ supply undervoltage positive going threshold	3.3	4.1	5		
$V_{CCUV}$	$V_{\text{CC}}$ and $V_{\text{BS}}$ supply undervoltage negative going threshold	3	3.8	4.7	V	
$V_{\text{CCUVH}}$ $V_{\text{BSUVH}}$	Hysteresis	0.05	0.3			
I <sub>O+</sub>	Output high short circuit pulsed current	_	200	_		$V_O = 0V$ , PW $\leq 10\mu$ s
I <sub>O-</sub>	Output low short circuit pulsed current	_	350	_	mA ·	V <sub>O</sub> = 15V, PW ≤ 10µs



# **Dynamic Electrical Characteristics**

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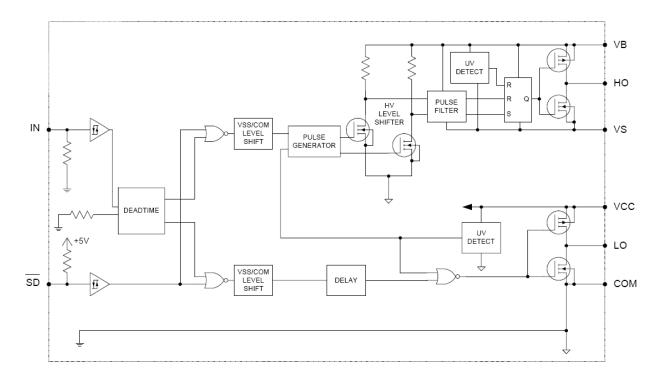
 $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V,  $C_L$  = 1000pF,  $T_A$  = 25°C unless otherwise specified.

Symbol	Definition	Min	Тур	Max	Units	Test conditions
t <sub>on</sub>	Turn-on propagation delay	450	650	850		V <sub>S</sub> = 0V
t <sub>off</sub>	Turn-off propagation delay	_	200	280		V <sub>S</sub> = 0V or 600V
t <sub>sd</sub>	Shut-down propagation delay	_	200	280		
MT	Delay matching, HS & LS turn-on/off	_	0	50		
t <sub>r</sub>	Turn-on rise time	_	130	220	ns	V = 0V
t <sub>f</sub>	Turn-off fall time	_	50	80		V <sub>S</sub> = 0V
DT	Deadtime: LO turn-off to HO turn-on (DT <sub>LO-HO</sub> ) & HO turn-off to LO turn-on (DT <sub>HO-LO</sub> )	300	450	600		
MDT	Deadtime matching = DT <sub>LO-HO</sub> – DT <sub>HO-LO</sub>		0	60		



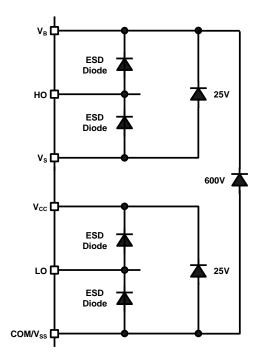
## **Functional Block Diagram:**

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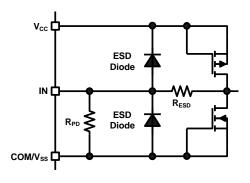


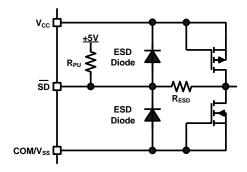


## **Input/Output Pin Equivalent Circuit Diagrams:**



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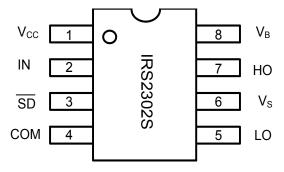




## **Lead Definitions:**

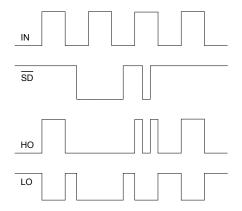
Symbol	Description
V <sub>CC</sub>	Low-side and logic fixed supply
IN	Logic input for high and low side gate driver outputs (HO and LO), in phase with HO
SD	Logic input for shutdown
СОМ	Low-side return
LO	Low-side gate drive output
Vs	High-side floating supply return
НО	High-side gate drive output
V <sub>B</sub>	High-side floating supply

## **Lead Assignments**





## **Application Information and Additional Details**



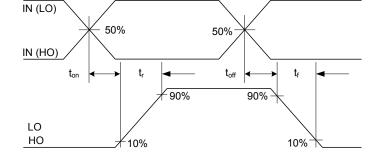
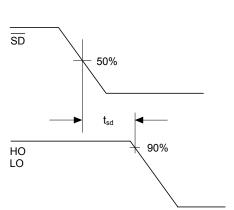


Figure 1. Input/Output Timing Diagram

Figure 2. Switching Time Waveform Definitions





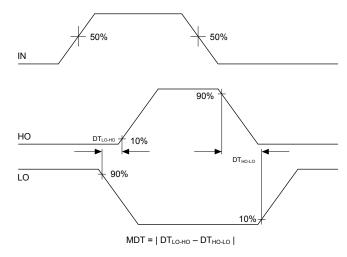


Figure 4. Deadtime Waveform Definitions

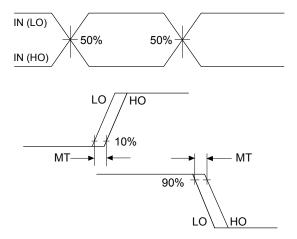


Figure 5. Delay Matching Waveform Definitions



## **Tolerability to Negative VS Transients**

The IRS2302S can withstand negative VS transient conditions on the order of -25V for a period of 100 ns ( $V_{BIAS}$  ( $V_{CC}$ ,  $V_{BS}$ ) = 15V and  $T_A$  = 25°C).

An illustration of the IRS2302S performance can be seen in Figure 6.

Even though the IRS2302S can handle these negative VS transient conditions, it is highly recommended that the circuit designer always limits the negative VS transients as much as possible with careful PCB layout and component use.

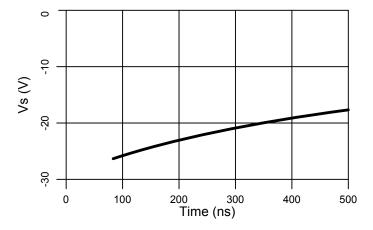


Figure 6: -Vs Transient results

MILLIMETERS

0.25

0.46

0.25

4.98

3.99

BASIC

BASIC

6.20

0.48

1.27

8\*

MIN

1.35

0.10

0.36

0.19

4.80

3.81

1.27

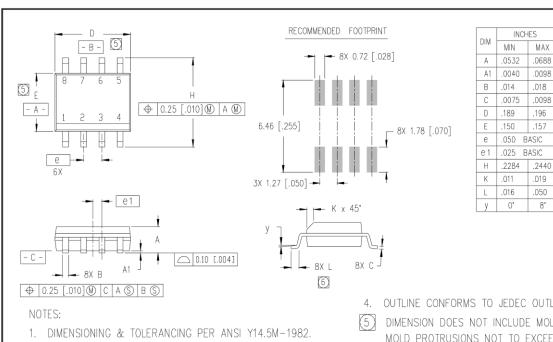
0.28

0.41

0\*



## **Package Details**



2. CONTROLLING DIMENSION: MILLIMETER.

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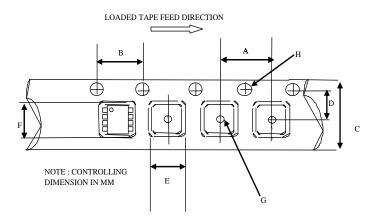
- 3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.006].
- (6) DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

### 8 Lead SOIC

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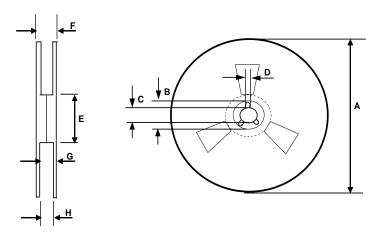


## **Tape and Reel Details**



#### CARRIER TAPE DIMENSION FOR 8SOICN

	Metric		Imperial		
Code	Min	Max	Min	Max	
Α	7.90	8.10	0.311	0.318	
В	3.90	4.10	0.153	0.161	
С	11.70	12.30	0.46	0.484	
D	5.45	5.55	0.214	0.218	
E	6.30	6.50	0.248	0.255	
F	5.10	5.30	0.200	0.208	
G	1.50	n/a	0.059	n/a	
Н	1.50	1.60	0.059	0.062	



REEL DIMENSIONS FOR 8SOICN

	Metric		Imperial	
Code	Min	Max	Min	Max
Α	329.60	330.25	12.976	13.001
В	20.95	21.45	0.824	0.844
С	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
Н	12.40	14.40	0.488	0.566



## **Part Marking Information**

